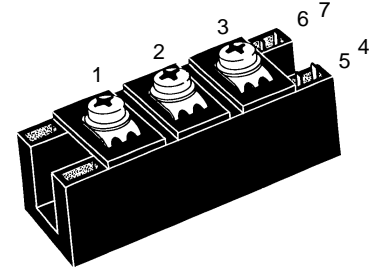


$$I_{TRMS} = 2 \times 300 \text{ A}$$

$$I_{TAVM} = 2 \times 130 \text{ A}$$

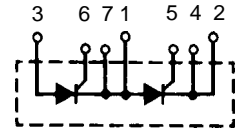
$$V_{RRM} = 800 - 1800 \text{ V}$$

V_{RSM}	V_{RRM}	Type	
V_{DSM}	V_{DRM}		
V	V		
900	800	WPT 132-08	WPH 132-08
1300	1200	WPT 132-12	WPH 132-12
1500	1400	WPT 132-14	WPH 132-14
1700	1600	WPT 132-16	WPH 132-16
1900	1800	WPT 132-18	WPH 132-18

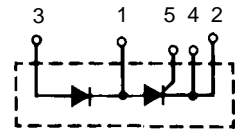


Symbol	Test Conditions	Maximum Ratings	
I_{TRMS}, I_{FRMS} I_{TAVM}, I_{FAVM}	$T_{VJ} = T_{VJM}$ $T_C = 85^\circ\text{C}; 180^\circ \text{ sine}$	300	A
		130	A
I_{TSM}, I_{FSM}	$T_{VJ} = 45^\circ\text{C};$ $V_R = 0$	t = 10 ms (50 Hz), sine t = 8.3 ms (60 Hz), sine	5500 A 5850 A
	$T_{VJ} = T_{VJM}$ $V_R = 0$	t = 10 ms (50 Hz), sine t = 8.3 ms (60 Hz), sine	4800 A 5100 A
$\int i^2 dt$	$T_{VJ} = 45^\circ\text{C}$ $V_R = 0$	t = 10 ms (50 Hz), sine t = 8.3 ms (60 Hz), sine	151 000 A ² s 142 000 A ² s
	$T_{VJ} = T_{VJM}$ $V_R = 0$	t = 10 ms (50 Hz), sine t = 8.3 ms (60 Hz), sine	115 000 A ² s 108 000 A ² s
$(di/dt)_{cr}$	$T_{VJ} = T_{VJM}$ f = 50 Hz, $t_p = 200 \mu\text{s}$ $V_D = 2/3 V_{DRM}$ $I_G = 0.5 \text{ A}$ $di_G/dt = 0.5 \text{ A}/\mu\text{s}$	repetitive, $I_T = 500 \text{ A}$ non repetitive, $I_T = 500 \text{ A}$	150 A/ μs 500 A/ μs
$(dv/dt)_{cr}$	$T_{VJ} = T_{VJM};$ $R_{GK} = \infty;$ method 1 (linear voltage rise)	$V_{DR} = 2/3 V_{DRM}$	1000 V/ μs
P_{GM}	$T_{VJ} = T_{VJM}$ $I_T = I_{TAVM}$	$t_p = 30 \mu\text{s}$ $t_p = 500 \mu\text{s}$	120 W 60 W
P_{GAV}			8 W
V_{RGM}			10 V
T_{VJ}			-40...+125 °C
T_{VJM}			125 °C
T_{stg}			-40...+125 °C
V_{ISOL}	50/60 Hz, RMS $I_{ISOL} \leq 1 \text{ mA}$	t = 1 min t = 1 s	3000 V~ 3600 V~
M_d	Mounting torque (M6) Terminal connection torque (M6)	2.25-2.75/20-25 4.5-5.5/40-48	Nm/lb.in. Nm/lb.in.
Weight	Typical including screws		125 g

WPT 132



WPH 132



Features

- International standard package
- Direct copper bonded Al_2O_3 -ceramic base plate
- Planar passivated chips
- Isolation voltage 3600 V~
- Keyed gate/cathode twin pins

Applications

- Motor control
- Power converter
- Heat and temperature control for industrial furnaces and chemical processes
- Lighting control
- Contactless switches

Advantages

- Space and weight savings
- Simple mounting
- Improved temperature and power cycling
- Reduced protection circuits

Symbol	Test Conditions	Characteristic Values
I_{RRM}, I_{DRM}	$T_{VJ} = T_{VJM}; V_R = V_{RRM}; V_D = V_{DRM}$	10 mA
V_T, V_F	$I_T, I_F = 300 \text{ A}; T_{VJ} = 25^\circ\text{C}$	1.36 V
V_{T0}	For power-loss calculations only ($T_{VJ} = 125^\circ\text{C}$)	0.8 V
r_T		1.5 mΩ
V_{GT}	$V_D = 6 \text{ V}; T_{VJ} = 25^\circ\text{C}$	2.5 V
	$T_{VJ} = -40^\circ\text{C}$	2.6 V
I_{GT}	$V_D = 6 \text{ V}; T_{VJ} = 25^\circ\text{C}$	150 mA
	$T_{VJ} = -40^\circ\text{C}$	200 mA
V_{GD}	$T_{VJ} = T_{VJM}; V_D = 2/3 V_{DRM}$	0.2 V
I_{GD}		10 mA
I_L	$T_{VJ} = 25^\circ\text{C}; t_p = 30 \mu\text{s}; V_D = 6 \text{ V}$ $I_G = 0.5 \text{ A}; di_G/dt = 0.5 \text{ A}/\mu\text{s}$	300 mA
I_H	$T_{VJ} = 25^\circ\text{C}; V_D = 6 \text{ V}; R_{GK} = \infty$	200 mA
t_{gd}	$T_{VJ} = 25^\circ\text{C}; V_D = 1/2 V_{DRM}$ $I_G = 0.5 \text{ A}; di_G/dt = 0.5 \text{ A}/\mu\text{s}$	2 μs
t_q	$T_{VJ} = T_{VJM}; I_T = 160 \text{ A}; t_p = 200 \mu\text{s}; -di/dt = 10 \text{ A}/\mu\text{s}$ typ. $V_R = 100 \text{ V}; dv/dt = 20 \text{ V}/\mu\text{s}; V_D = 2/3 V_{DRM}$	150 μs
Q_s	$T_{VJ} = T_{VJM}; I_T, I_F = 300 \text{ A}, -di/dt = 50 \text{ A}/\mu\text{s}$	550 μC
I_{RM}		235 A
R_{thJC}	per thyristor/diode; DC current per module	0.23 K/W
R_{thJK}	per thyristor/diode; DC current per module	0.33 K/W
	other values see Fig. 8/9	0.115 K/W
		0.165 K/W
d_s	Creepage distance on surface	12.7 mm
d_A	Strike distance through air	9.6 mm
a	Maximum allowable acceleration	50 m/s ²

Optional accessories for modules

Keyed gate/cathode twin plugs with wire length = 350 mm, gate = yellow, cathode = red

Type **U9911** UL 758, style 1385, CSA class 5851, guide 460-1-1

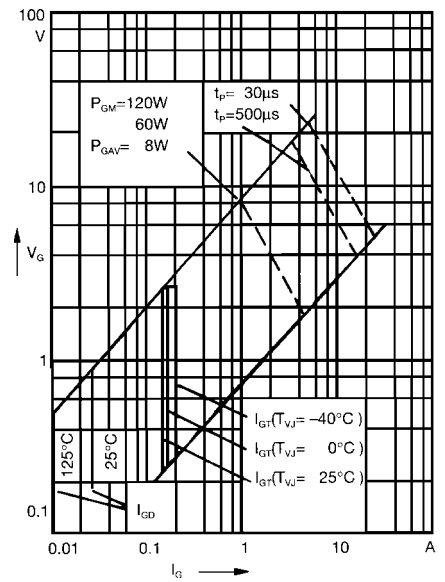


Fig. 1 Gate trigger characteristics

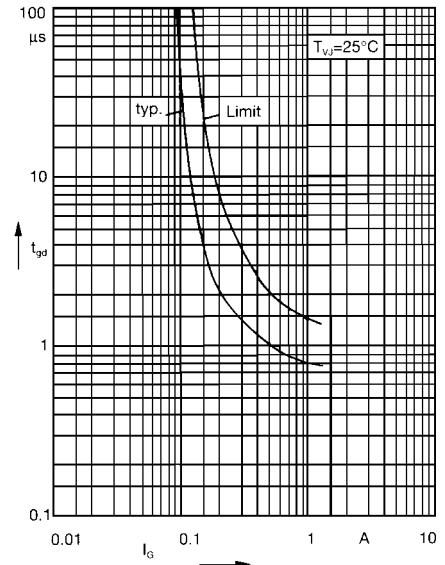
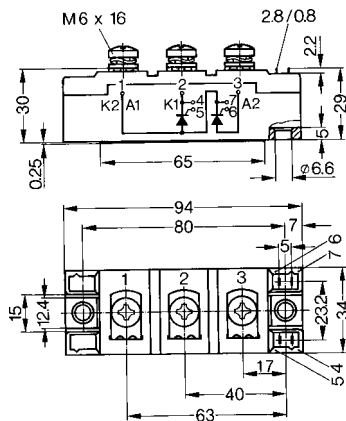
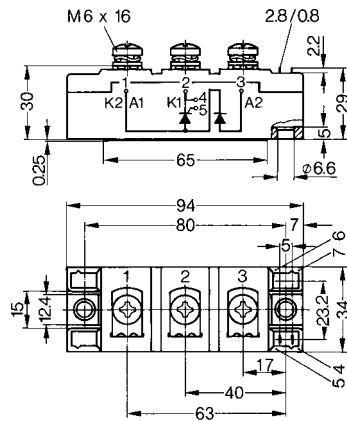


Fig. 2 Gate trigger delay time

Dimensions in mm (1 mm = 0.0394")
WPT 132



WPH 132



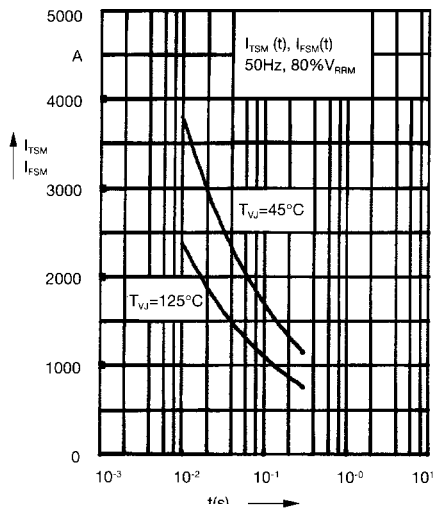


Fig. 3 Surge overload current
 I_{TSM} , I_{FSM} : Crest value, t: duration

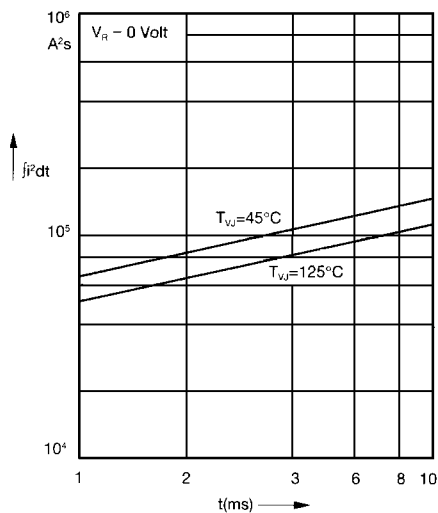


Fig. 4 $\int i^2 dt$ versus time (1-10 ms)

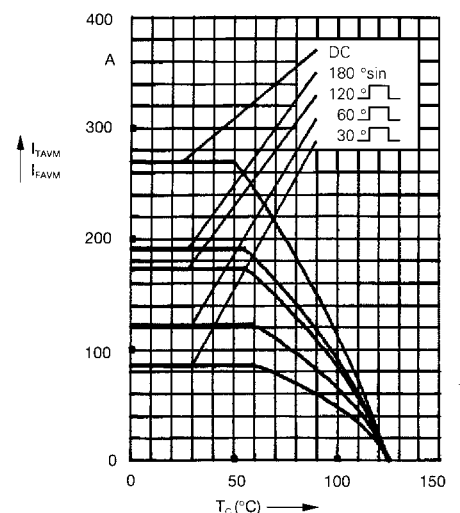


Fig. 4a Maximum forward current at case temperature

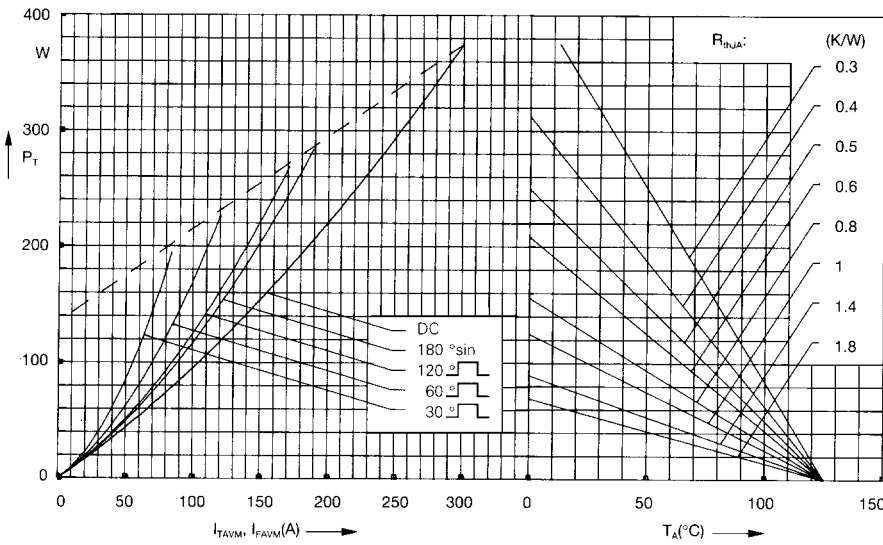


Fig. 5 Power dissipation versus on-state current and ambient temperature (per thyristor or diode)

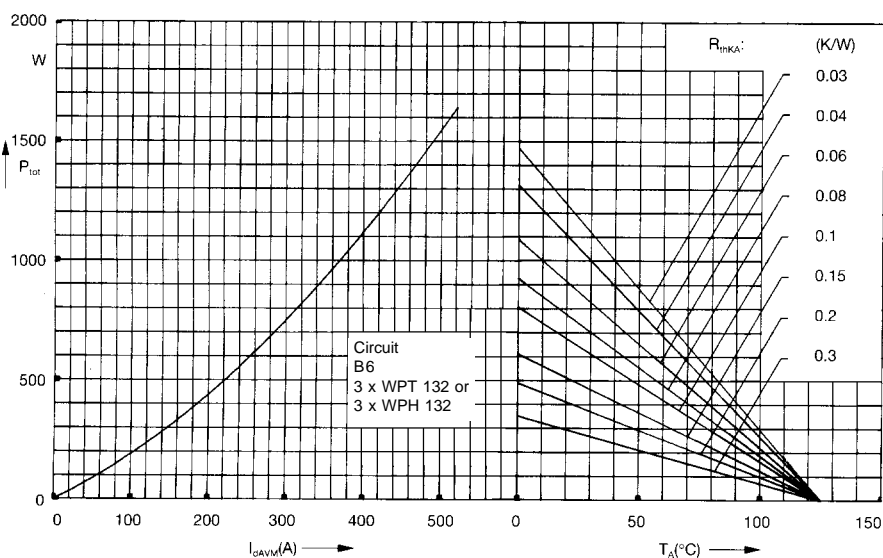


Fig. 6 Three phase rectifier bridge: Power dissipation versus direct output current and ambient temperature

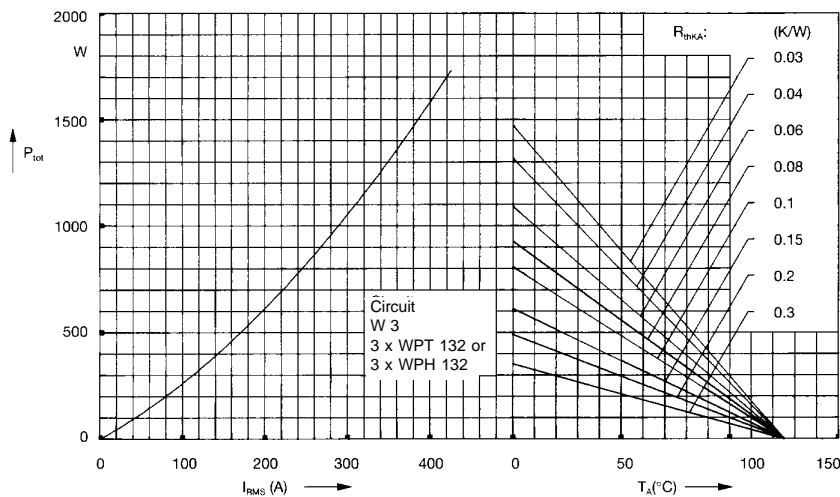


Fig. 7 Three phase AC-controller:
Power dissipation versus RMS
output current and ambient
temperature

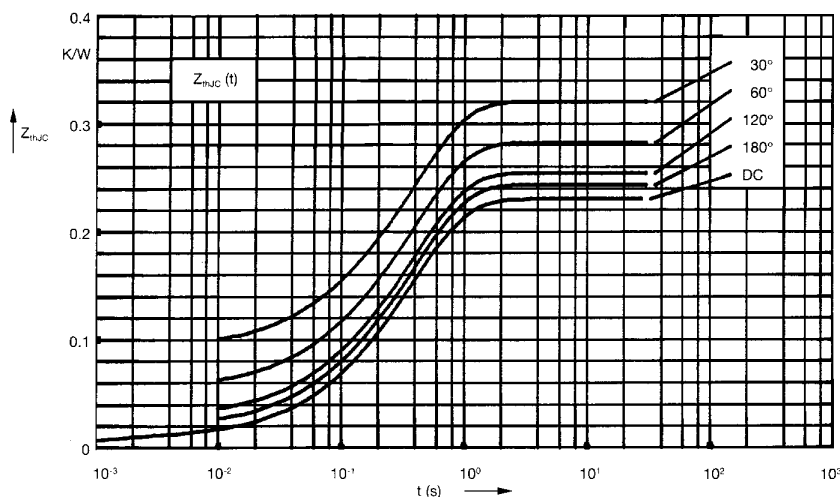


Fig. 8 Transient thermal impedance junction
to case (per thyristor or diode)

R_{thJC} for various conduction angles d:

d	R_{thJC} (K/W)
DC	0.230
180°	0.244
120°	0.255
60°	0.283
30°	0.321

Constants for Z_{thJC} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.0095	0.001
2	0.0175	0.065
3	0.203	0.4

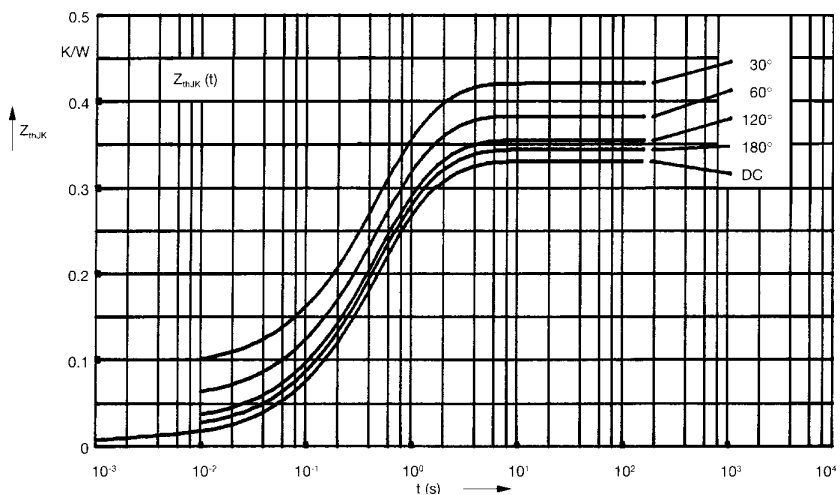


Fig. 9 Transient thermal impedance junction
to heatsink (per thyristor or diode)

R_{thJK} for various conduction angles d:

d	R_{thJK} (K/W)
DC	0.330
180°	0.344
120°	0.355
60°	0.383
30°	0.421

Constants for Z_{thJK} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.0095	0.001
2	0.0175	0.065
3	0.203	0.4
4	0.1	1.29

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